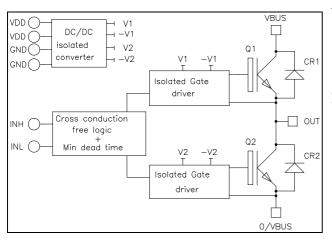
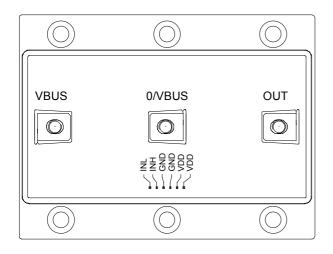


Phase leg Intelligent Power Module





# APTLGL325A1208G

## $V_{CES} = 1200V$ $I_{C} = 325A$ @ $Tc = 80^{\circ}C$

#### Application

- Motor control
- Uninterruptible Power Supplies
- Switched Mode Power Supplies
- Amplifier

## Features

- Trench + Field Stop IGBT 4 Technology
- Low voltage drop
- Low leakage current
- Low switching losses
- Soft recovery parallel diodes
- Low diode VF
- RBSOA and SCSOA rated
- Integrated Fail Safe IGBT Protection (Driver)
  - Top Bottom input signals Interlock
  - Isolated DC/DC Converter
- Low stray inductance
- M5 power connectors
- High level of integration

#### Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Very high noise immunity (common mode rejection > 25kV/µs)
- Galvanic Isolation: 3750V for the optocoupler 2500V for the transformer
- 5V logic level with Schmitt-trigger Input
- Single  $V_{DD}$ =5V supply required
- Secondary auxiliary power supplies internally generated (15V, -6V)
- Optocoupler qualified to AEC-Q100 test guidelines
- RoHS compliant

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com APTLGL325A1208G - Rev 1 October, 2012



## All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

### 1. Inverter Power Module

## Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V <sub>CES</sub>	Collector - Emitter Breakdown Voltage		1200	V
т	Continuous Collector Current	$T_C = 25^{\circ}C$	420	
I <sub>C</sub>	$T_{\rm C} = 80$		325	Α
I <sub>CM</sub>	Pulsed Collector Current	$T_C = 25^{\circ}C$	600	
P <sub>D</sub>	Maximum Power Dissipation	$T_C = 25^{\circ}C$	1500	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^{\circ}C$	600A @ 1150V	

### **Electrical Characteristics**

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I <sub>CES</sub>	Zero Gate Voltage Collector Current	$V_{GE} = 0V$	$T_j = 25^{\circ}C$			500	μA
		$V_{CE} = 1200V$	$T_{j} = 150^{\circ}C$			750	μΑ
V <sub>CE(sat)</sub>	Collector Emitter Saturation Voltage	$V_{DD} = V_{IN} = 5V$	$T_j = 25^{\circ}C$		1.85	2.2	V
		$I_{\rm C} = 300 {\rm A}$	$T_{j} = 150^{\circ}C$		2.2		v

## **Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$		17.6		
Coes	Output Capacitance	$V_{CE} = 25V$		1.16		nF
C <sub>res</sub>	Reverse Transfer Capacitance	f = 1 MHz		0.94		
T <sub>r</sub>	Rise Time	Inductive Switching (25°C) V = V = 5V		30		nc
$T_{\rm f}$	Fall Time	$V_{DD} = V_{IN} = 5V$ $V_{Bus} = 600V$ ; $I_C = 300A$		70		ns
Tr	Rise Time	Inductive Switching (150°C)		40		20
$T_{\rm f}$	Fall Time	$V_{DD} = V_{IN} = 5V$ $V_{Bus} = 600V$ $I_{C} = 300A$		80		ns
Eon	Turn-on Switching Energy			34		т
E <sub>off</sub>	Turn-off Switching Energy			29		mJ
I <sub>sc</sub>	Short Circuit data	$V_{DD} = V_{IN} = 5V; V_{Bus} = 900V$ $t_p \le 10 \mu s; T_i = 150^{\circ}C$		1100		А
R <sub>thJC</sub>	Junction to Case thermal resistance				0.1	°C/W



## APTLGL325A1208G

#### **Reverse diode ratings and characteristics**

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit		
V <sub>RRM</sub>	Maximum Peak Repetitive Reverse Voltage			1200			V		
I <sub>RM</sub>	Maximum Reverse Leakage Current	V <sub>R</sub> =1200V	$T_i = 25^{\circ}C$			250	μA		
-101		· K -= • • •	$T_{i} = 150^{\circ}C$			750	P*		
I <sub>F</sub>	DC Forward Current		$Tc = 80^{\circ}C$		360		A		
$V_{\rm F}$	Diode Forward Voltage	$I_{\rm F} = 300 {\rm A}$	$T_i = 25^{\circ}C$		1.7	2.2	V		
• F			$T_{i} = 150^{\circ}C$		1.65		v		
t <sub>rr</sub>	Reverse Recovery Time		$T_j = 25^{\circ}C$		155		ns		
ι <sub>rr</sub>	Reverse Recovery Time		$T_{j} = 150^{\circ}C$		300		115		
Q <sub>rr</sub>	Reverse Recovery Charge	$I_{\rm F} = 300 \text{A}$ $V_{\rm R} = 600 \text{V}$	$T_j = 25^{\circ}C$		29		μC		
Qrr	Reverse Recovery Charge	$v_{\rm R} = 000 v$ di/dt =7000A/µs			$T_{j} = 150^{\circ}C$		61		μΟ
F	E <sub>rr</sub> Reverse Recovery Energy		$T_j = 25^{\circ}C$		10.4		mJ		
Ľ'n		$T_{j} = 150^{\circ}C$		22		1113			
R <sub>thJC</sub>	Junction to Case Thermal Resistance					0.17	°C/W		

#### 2. Driver

## Absolute maximum ratings

Symbol		Parameter	Max ratings	Unit
$V_{DD}$	Supply Voltage		5.5	V
V <sub>INi</sub>	Input signal voltage i=L, H		5.5	v
I <sub>VDDmax</sub>	Maximum Supply current $\frac{V_{INi} = 0V, i = L \& H}{V_{DD} = 5V, V_{INH} = /V_{INL}; F_{out} = 55 \text{kHz}}$	$V_{INi} = 0V, i = L \& H$	0.35	
		2	A	
$\mathbf{f}_{max}$	Maximum Switching Frequen	cy	55	kHz

## **Driver Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
V <sub>DD</sub>	Operating Supply Voltage		4.5	5	5.5	V
V <sub>INi(max)</sub>	Maximum Input Voltage		-0.5	5	5.5	
V <sub>INi (th+)</sub>	Positive Going Threshold Voltage	i = L, H		3.2		V
V <sub>INi(th-)</sub>	Negative Going Threshold Voltage	1 – L, II		1		
R <sub>INi</sub>	Input Resistance *	1		1		kΩ
T <sub>d(on)</sub>	Turn On delay time	Driver + IGBT		1100 <sup>0</sup>		
D <sub>T</sub>	Built in dead time			600		ns
T <sub>d(off)</sub>	Turn Off delay time	Driver + IGBT		750		
PWD	Pulse Width Distortion				300	
PDD	Propagation Delay Difference between any two driver	T <sub>d(on)</sub> - T <sub>d(off)</sub>	-350		350	ns
V <sub>ISOL</sub>	Primary to Secondary Isolation		2500			$V_{RMS}$

\* Low impedance guarantees good noise immunity.

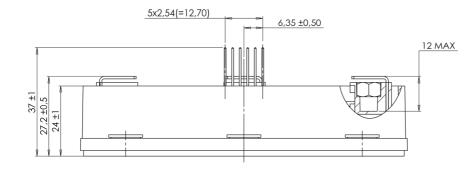
• Including built in dead time.

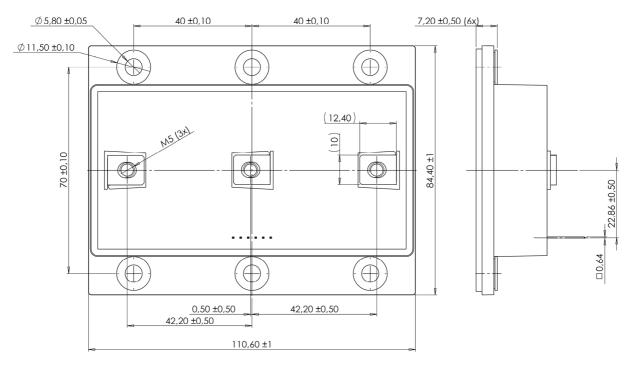


## 3. Package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit			
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t =	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz					V			
T <sub>J</sub>	Operating junction temperature range	Operating junction temperature range-40150				150				
T <sub>OP</sub>	Operating Ambient Temperature			-40		85	°C			
T <sub>STG</sub>	Storage Temperature Range			-40		100	)0			
T <sub>C</sub>	Operating Case Temperature		-40		100					
Torqua	Mounting torque To heatsink M5   For terminals M5	To heatsink	M5	2		4.7	N.m			
Torque		M5	2		4	19.111				
Wt	Package Weight				550		g			

## 4. LP8 Package outline (dimensions in mm)

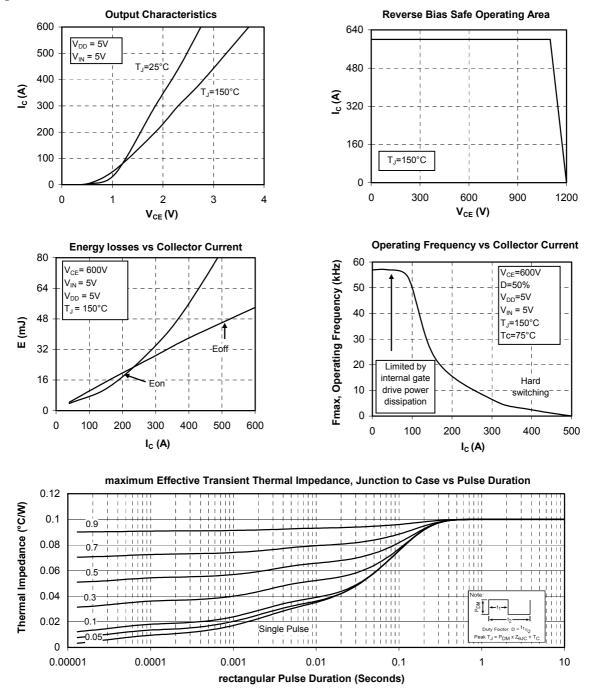






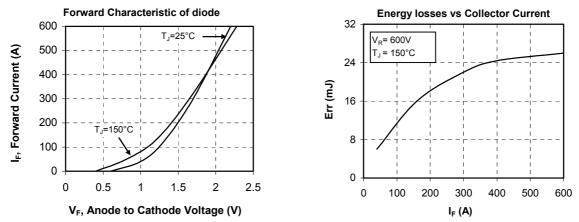
## **APTLGL325A1208G**

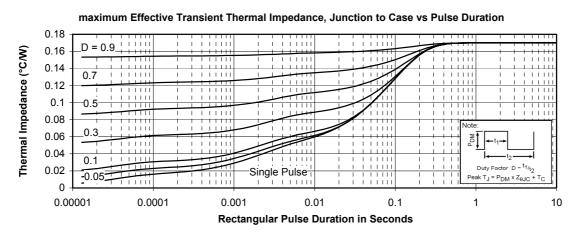
#### **Typical IGBT Performance Curve**





#### **Typical diode Performance Curve**









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